

## 54ABT543

# Octal Registered Transceiver with TRI-STATE® Outputs

### General Description

The 'ABT543 octal transceiver contains two sets of D-type latches for temporary storage of data flowing in either direction. Separate Latch Enable and Output Enable inputs are provided for each register to permit independent control of inputting and outputting in either direction of data flow.

### Features

- Back-to-back registers for storage
- Bidirectional data path

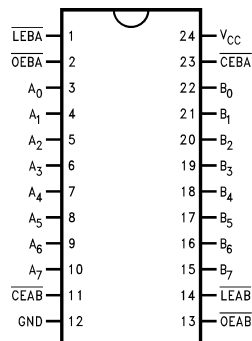
- A and B outputs have current sourcing capability of 24 mA and current sinking capability of 48 mA
- Separate controls for data flow in each direction
- Guaranteed latching protection
- High impedance glitch free bus loading during entire power up and power down cycle
- Nondestructive hot insertion capability
- Standard Military Drawing (SMD) 5962-9231401

### Ordering Code:

Military	Package Number	Package Description
54ABT543J-QML	J24F	24-Lead Ceramic Dual-In-Line
54ABT543W-QML	W24C	24-Lead Cerpack
54ABT543E-QML	E28A	28-Lead Ceramic Leadless Chip Carrier, Type C

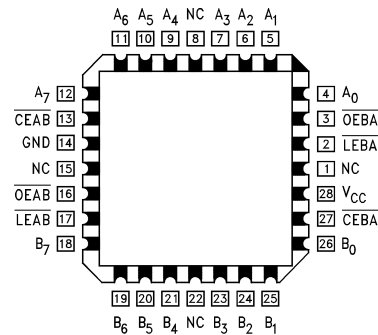
### Connection Diagrams

Pin Assignment for  
DIP and Flatpak



10021801

Pin Assignment  
for LCC



10021802

## Pin Descriptions

Pin Names	Description
$\overline{OEAB}$ , $\overline{OEBA}$	Output Enable Inputs
$\overline{LEAB}$ , $\overline{LEBA}$	Latch Enable Inputs
$\overline{CEAB}$ , $\overline{CEBA}$	Chip Enable Inputs
$A_0$ – $A_7$	Side A Inputs or TRI-STATE Outputs
$B_0$ – $B_7$	Side B Inputs or TRI-STATE Outputs

## Functional Description

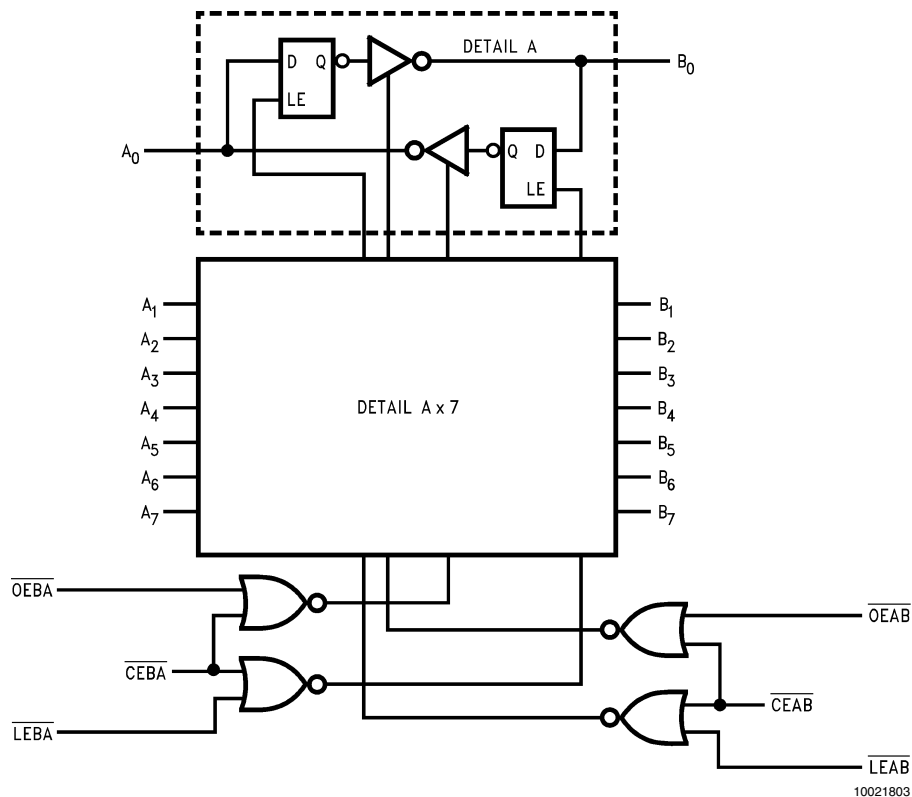
The 'ABT543 contains two sets of D-type latches, with separate input and output controls for each. For data flow from A to B, for example, the A to B Enable ( $\overline{CEAB}$ ) input must be low in order to enter data from the A port or take data from the B port as indicated in the Data I/O Control Table. With  $\overline{CEAB}$  low, a low signal on ( $\overline{LEAB}$ ) input makes the A to B latches transparent; a subsequent low to high transition of the  $\overline{LEAB}$  line puts the A latches in the storage mode and their outputs no longer change with the A inputs. With  $\overline{CEAB}$  and  $\overline{OEAB}$  both low, the B output buffers are active and reflect the data present on the output of the A latches. Control of data flow from B to A is similar, but using the  $\overline{CEBA}$ ,  $\overline{LEBA}$  and  $\overline{OEBA}$ .

Data I/O Control Table

Inputs			Latch Status	Output Buffers
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$		
H	X	X	Latched	High Z
X	H	X	Latched	—
L	L	X	Transparent	—
X	X	H	—	High Z
L	X	L	—	Driving

H = High Voltage Level  
L = Low Voltage Level  
X = Immaterial

## Logic Diagram



**Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	-65°C to +150°C
Ambient Temperature under Bias	-55°C to +125°C
Junction Temperature under Bias	
Ceramic	-55°C to +175°C
V <sub>CC</sub> Pin Potential to	
Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA
Voltage Applied to Any Output	
in the Disable or Power-Off State	-0.5V to +5.5V
in the HIGH State	-0.5V to V <sub>CC</sub>
Current Applied to Output	

in LOW State (Max)	twice the rated I <sub>OL</sub> (mA)
DC Latchup Source Current	-500 mA
Over Voltage Latchup (I/O)	10V

**Recommended Operating Conditions**

Free Air Ambient Temperature	
Military	-55°C to +125°C
Supply Voltage	
Military	+4.5V to +5.5V
Minimum Input Edge Rate	(ΔV/Δt)
Data Input	50 mV/ns
Enable Input	20 mV/ns
Clock Input	100 mV/ns

**DC Electrical Characteristics**

Symbol	Parameter	ABT543			Units	V <sub>CC</sub>	Conditions
		Min	Typ	Max			
V <sub>IH</sub>	Input HIGH Voltage	2.0			V		Recognized HIGH Signal
V <sub>IL</sub>	Input LOW Voltage			0.8	V		Recognized LOW Signal
V <sub>CD</sub>	Input Clamp Diode Voltage			-1.2	V	Min	I <sub>IN</sub> = -18 mA (Non I/O Pins)
V <sub>OH</sub>	Output HIGH Voltage	54ABT	2.5		V	Min	I <sub>OH</sub> = -3 mA, (A <sub>n</sub> , B <sub>n</sub> )
		54ABT	2.0				
V <sub>OL</sub>	Output LOW Voltage	54ABT		0.55	V	Min	I <sub>OL</sub> = 48 mA, (A <sub>n</sub> , B <sub>n</sub> )
V <sub>ID</sub>	Input Leakage Test		4.75		V	0.0	I <sub>ID</sub> = 1.9 μA, (Non-I/O Pins) All Other Pins Grounded
I <sub>IH</sub>	Input HIGH Current			5	μA	Max	V <sub>IN</sub> = 2.7V (Non-I/O Pins) (Note 3) V <sub>IN</sub> = V <sub>CC</sub> (Non-I/O Pins)
I <sub>BVI</sub>	Input HIGH Current Breakdown Test			7	μA	Max	V <sub>IN</sub> = 7.0V (Non-I/O Pins)
I <sub>BVIT</sub>	Input HIGH Current Breakdown Test (I/O)			100	μA	Max	V <sub>IN</sub> = 5.5V (A <sub>n</sub> , B <sub>n</sub> )
I <sub>IL</sub>	Input LOW Current			-5	μA	Max	V <sub>IN</sub> = 0.5V (Non-I/O Pins)(Note 3) V <sub>IN</sub> = 0.0V (Non-I/O Pins)
I <sub>IH</sub> + I <sub>OZH</sub>	Output Leakage Current			50	μA	0V-5.5V	V <sub>OUT</sub> = 2.7V (A <sub>n</sub> , B <sub>n</sub> ); OEAB or CEAB = 2V
I <sub>IL</sub> + I <sub>OZL</sub>	Output Leakage Current			-50	μA	0V-5.5V	V <sub>OUT</sub> = 0.5V (A <sub>n</sub> , B <sub>n</sub> ); OEAB or CEAB = 2V
I <sub>OS</sub>	Output Short-Circuit Current	-100	-275		mA	Max	V <sub>OUT</sub> = 0V (A <sub>n</sub> , B <sub>n</sub> )
I <sub>CEx</sub>	Output HIGH Leakage Current			50	μA	Max	V <sub>OUT</sub> = V <sub>CC</sub> (A <sub>n</sub> , B <sub>n</sub> )
I <sub>ZZ</sub>	Bus Drainage Test			100	μA	0.0V	V <sub>OUT</sub> = 5.5V (A <sub>n</sub> , B <sub>n</sub> ); All Others GND
I <sub>CCLH</sub>	Power Supply Current			50	μA	Max	All Outputs HIGH
I <sub>CCL</sub>	Power Supply Current			30	mA	Max	All Outputs LOW
I <sub>CCZ</sub>	Power Supply Current			50	μA	Max	Outputs TRI-STATE All Others at V <sub>CC</sub> or GND

## DC Electrical Characteristics (Continued)

Symbol	Parameter	ABT543			Units	V <sub>CC</sub>	Conditions
		Min	Typ	Max			
I <sub>CC</sub> T	Additional I <sub>CC</sub> /Input		2.5		mA	Max	V <sub>I</sub> = V <sub>CC</sub> - 2.1V All Others at V <sub>CC</sub> or GND
I <sub>CC</sub> D	Dynamic I <sub>CC</sub> No Load (Note 3)		0.18		mA/MHz	Max	Outputs Open, $\overline{CEAB}$ and $\overline{OEAB} = \text{GND}, \overline{CEBA} =$ V <sub>CC</sub> , One Bit Toggling, 50% Duty Cycle, (Note 4)

**Note 1:** Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

**Note 2:** Either voltage limit or current limit is sufficient to protect inputs.

**Note 3:** Guaranteed but not tested.

**Note 4:** For 8-bit toggling. I<sub>CC</sub>D < 1.4 mA/MHz.

## DC Electrical Characteristics

Symbol	Parameter	Min	Max	Units	V <sub>CC</sub>	Conditions
						C <sub>L</sub> = 50 pF, R <sub>L</sub> = 500Ω
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>		1.1	V	5.0	T <sub>A</sub> = 25°C (Note 5)
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>		-0.45	V	5.0	T <sub>A</sub> = 25°C (Note 5)

**Note 5:** Max number of outputs defined as (n). n - 1 data inputs are driven 0V to 3V. One output at LOW.

## AC Electrical Characteristics

Symbol	Parameter	54ABT		Units	Fig. No.
		T <sub>A</sub> = -55°C to +125°C V <sub>CC</sub> = 4.5V-5.5V C <sub>L</sub> = 50 pF			
		Min	Max		
t <sub>PLH</sub>	Propagation Delay	1.6	6.4	ns	Figure 4
t <sub>PHL</sub>	A <sub>n</sub> to B <sub>n</sub> or B <sub>n</sub> to A <sub>n</sub>	1.6	6.2		
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay $\overline{LEAB}$ to B <sub>n</sub> , $\overline{LEBA}$ to A <sub>n</sub>	1.6	6.6	ns	Figure 4
	$\overline{OEBA}$ or $\overline{OEAB}$ to A <sub>n</sub> or B <sub>n</sub>	1.6	6.4		
t <sub>PZH</sub> t <sub>PZL</sub>	Enable Time $\overline{LEAB}$ to B <sub>n</sub> , $\overline{LEBA}$ to A <sub>n</sub>	1.3	6.4	ns	Figure 6
	$\overline{OEBA}$ or $\overline{OEAB}$ to A <sub>n</sub> or B <sub>n</sub>	1.8	7.4		
t <sub>PHZ</sub>	Disable Time	2.0	7.2	ns	Figure 6
t <sub>PLZ</sub>	$\overline{CEBA}$ or $\overline{CEAB}$ to A <sub>n</sub> or B <sub>n</sub>	1.5	7.0		

## AC Operating Requirements

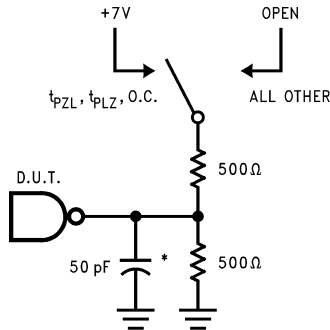
Symbol	Parameter	54ABT		Units	Fig. No.
		T <sub>A</sub> = -55°C to +125°C V <sub>CC</sub> = 4.5V-5.5V C <sub>L</sub> = 50 pF			
		Min	Max		
t <sub>S</sub> (H)	Setup Time, HIGH or LOW	3.5		ns	Figure 7
t <sub>S</sub> (L)	A <sub>n</sub> or B <sub>n</sub> to $\overline{\text{LEBA}}$ or $\overline{\text{LEAB}}$	3.0			
t <sub>H</sub> (H)	Hold Time, HIGH or LOW	2.0		ns	Figure 7
t <sub>H</sub> (L)	A <sub>n</sub> or B <sub>n</sub> to $\overline{\text{LEBA}}$ or $\overline{\text{LEAB}}$	2.0			
t <sub>S</sub> (H)	Setup Time, HIGH or LOW	3.3		ns	Figure 7
t <sub>S</sub> (L)	A <sub>n</sub> or B <sub>n</sub> to $\overline{\text{CEAB}}$ or $\overline{\text{CEBA}}$	2.5			
t <sub>H</sub> (H)	Hold Time, HIGH or LOW	2.0		ns	Figure 7
t <sub>H</sub> (L)	A <sub>n</sub> or B <sub>n</sub> to $\overline{\text{CEAB}}$ or $\overline{\text{CEBA}}$	2.0			
t <sub>W</sub> (L)	Pulse Width, LOW	3.5		ns	Figure 5

## Capacitance

Symbol	Parameter	Typ	Units	Conditions: T <sub>A</sub> = 25°C
C <sub>IN</sub>	Input Capacitance	5.0	pF	V <sub>CC</sub> = 0V (non I/O pins)
C <sub>I/O</sub> (Note 6)	Output Capacitance	11.0	pF	V <sub>CC</sub> = 5.0V (A <sub>n</sub> , B <sub>n</sub> )

**Note 6:** C<sub>I/O</sub> is measured at frequency, f = 1 MHz, PER MIL-STD-883, METHOD 3012.

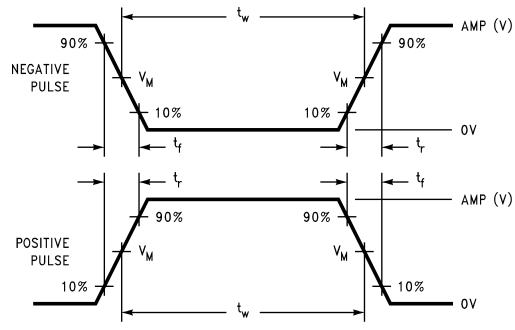
## AC Loading



10021804

\*Includes jig and probe capacitance

**FIGURE 1. Standard AC Test Load**



10021806

**FIGURE 2. V<sub>M</sub> = 1.5V  
Input Pulse Requirements**

Amplitude	Rep. Rate	t <sub>w</sub>	t <sub>r</sub>	t <sub>f</sub>
3V	1 MHz	500 ns	2.5 ns	2.5 ns

**FIGURE 3. Test Input Signal Requirements**

AC Loading (Continued)

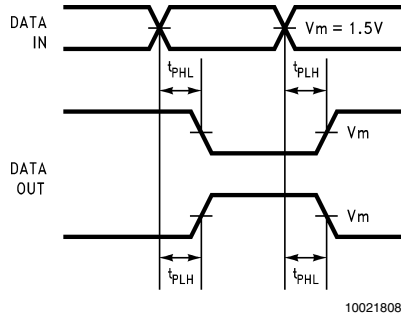


FIGURE 4. Propagation Delay Waveforms for Inverting and Non-Inverting Functions

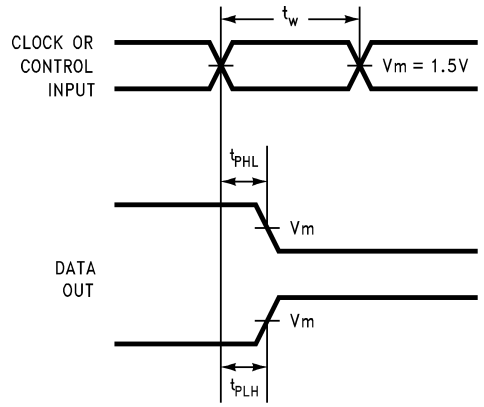


FIGURE 5. Propagation Delay, Pulse Width Waveforms

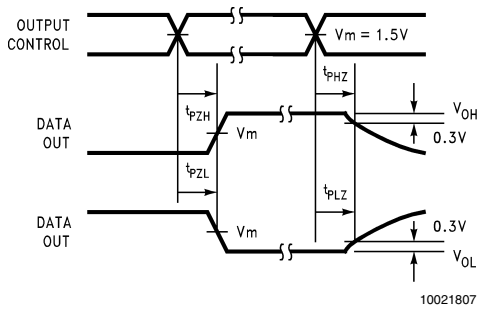


FIGURE 6. TRI-STATE Output HIGH and LOW Enable and Disable Times

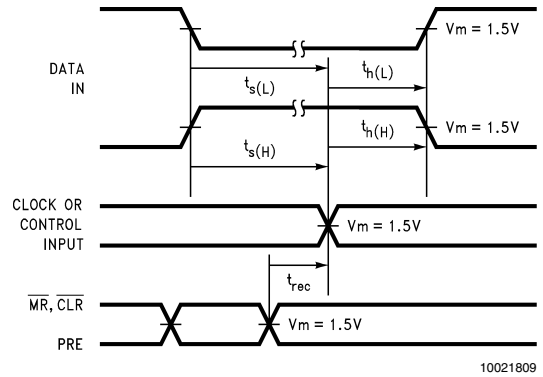
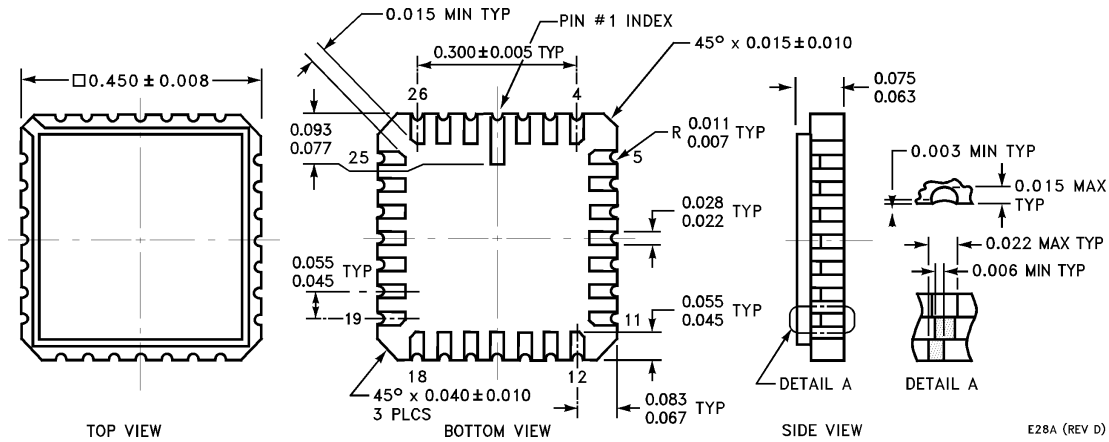


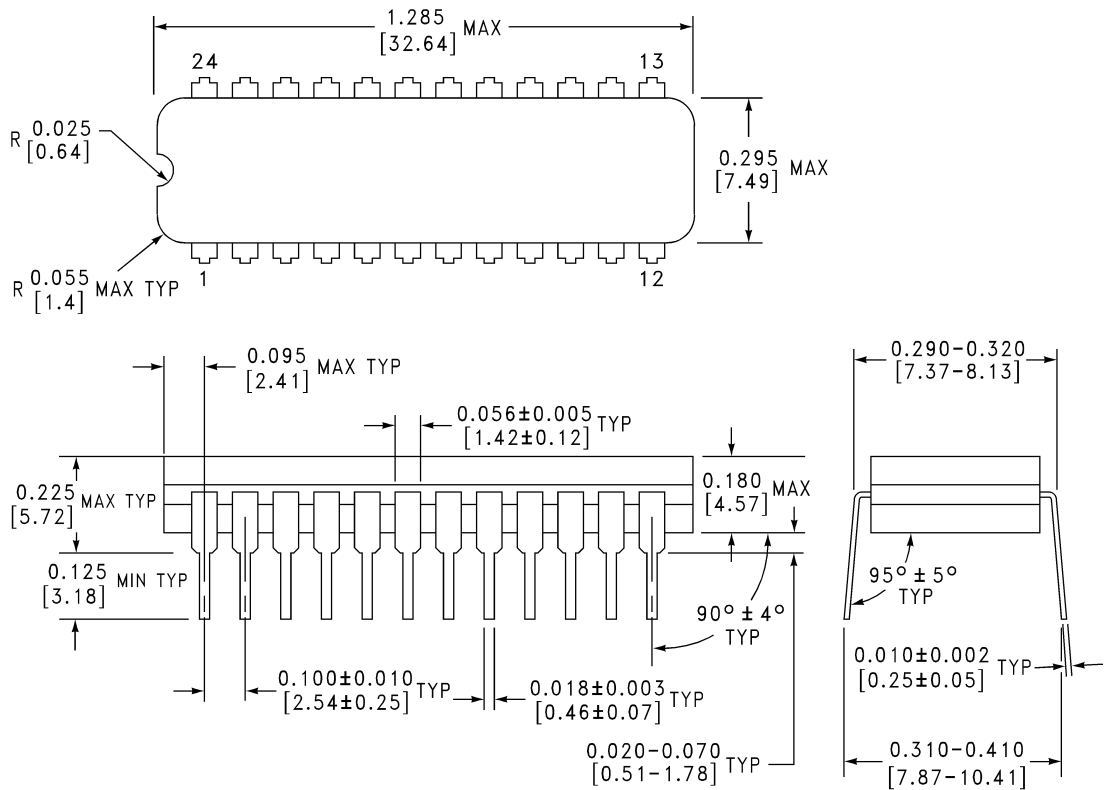
FIGURE 7. Setup Time, Hold Time and Recovery Time Waveforms

**Physical Dimensions** inches (millimeters)

unless otherwise noted



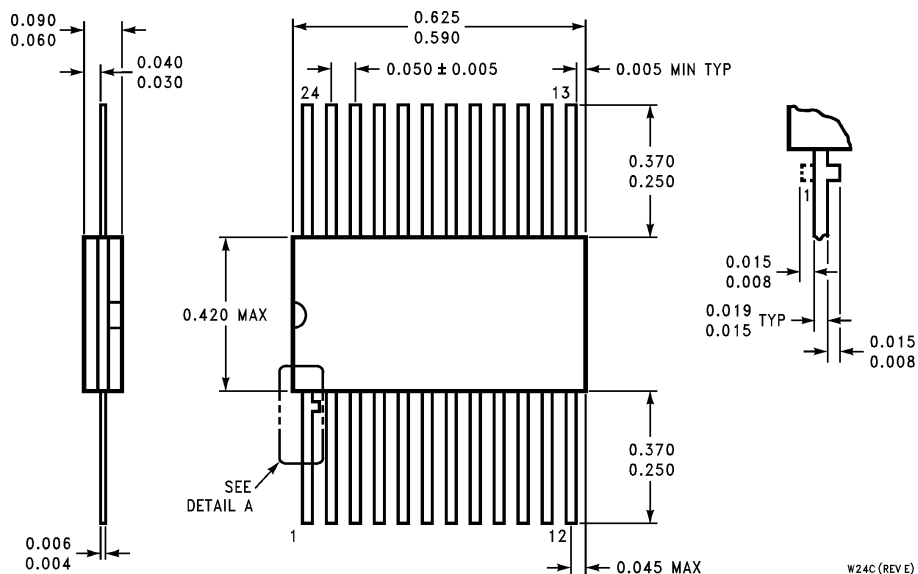
**28-Lead Ceramic Leadless Chip Carrier (L)**  
**Order Number 54ABT543E-QML**  
**NS Package Number E28A**



**24-Lead Ceramic Dual-In-Line Package**  
**Order Number 54ABT543J-QML**  
**NS Package Number J24F**

J24F (REV. H)

**Physical Dimensions** inches (millimeters) unless otherwise noted (Continued)



**24-Lead Ceramic Flatpak Package (F)**  
**Order Number 54ABT543W-QML**  
**NS Package Number W24C**

W24C (REV E)

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